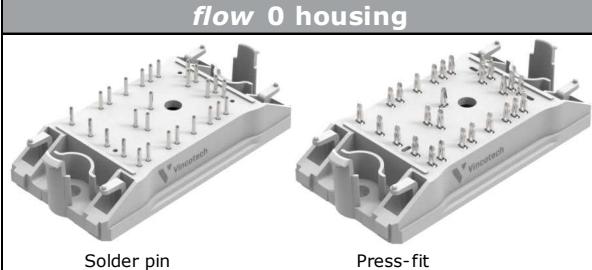
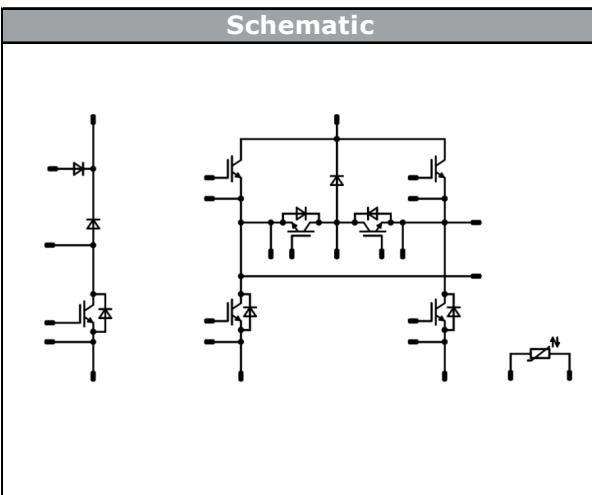




10-FZ07BVA020SM-LD44E08
10-PZ07BVA020SM-LD44E08Y
target datasheet

Vincotech

flow SOL 0		650 V / 20 A
Features		flow 0 housing
• For one-phase solar applications • Booster + Innovative H6.5 topology • LVRT (Low voltage ride through) capability • Ultra Fast IGBT H5 • NTC		 Solder pin Press-fit
Target applications		Schematic
• Solar Inverters		
Types		
• 10-FZ07BVA020SM-LD44E08 • 10-PZ07BVA020SM-LD44E08Y		

Maximum Ratings

$T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Condition	Value	Unit
Input Boost Switch				
Collector-emitter voltage	V_{CES}		650	V
Collector current	I_C	$T_j = T_{jmax}$ $T_s = 80^\circ\text{C}$	24	A
Repetitive peak collector current	I_{CRM}	t_p limited by T_{jmax}	60	A
Turn off safe operating area		$T_j \leq 150^\circ\text{C}$, $V_{CE} \leq 650\text{ V}$	40	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ $T_s = 80^\circ\text{C}$	49	W
Gate-emitter voltage	V_{GES}		± 20	V
Maximum Junction Temperature	T_{jmax}		175	$^\circ\text{C}$



Vincotech

Maximum Ratings

$T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Condition	Value	Unit
Input Boost Diode				
Peak repetitive reverse voltage	V_{RRM}		650	V
Continuous (direct) forward current	I_F	$T_j = T_{jmax}$ $T_s = 80^\circ\text{C}$	28	A
Repetitive peak forward current	I_{FRM}		40	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ $T_s = 80^\circ\text{C}$	52	W
Maximum junction temperature	T_{jmax}		175	$^\circ\text{C}$
Input Boost Sw. Protection Diode				
Peak Repetitive Reverse Voltage	V_{RRM}		650	V
Continuous (direct) forward current	I_F	$T_j=T_{jmax}$ $T_h=80^\circ\text{C}$	8	A
Repetitive peak forward current	I_{FRM}		12	A
Total power dissipation	P_{tot}	$T_j=T_{jmax}$ $T_h=80^\circ\text{C}$	10	W
Maximum Junction Temperature	T_{jmax}		175	$^\circ\text{C}$
ByPass Diode				
Peak Repetitive Reverse Voltage	V_{RRM}		1600	V
Continuous (direct) forward current	I_F	$T_j = T_{jmax}$ $T_s = 80^\circ\text{C}$	33	A
Surge (non-repetitive) forward current	I_{FSM}	50 Hz Single Half Sine Wave $t_p = 10 \text{ ms}$	200	A
Surge current capability	I^2t		200	A^2s
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ $T_s = 80^\circ\text{C}$	43	W
Maximum Junction Temperature	T_{jmax}		150	$^\circ\text{C}$
Boost Switch				
Collector-emitter voltage	V_{CES}		650	V
Collector current	I_C	$T_j = T_{jmax}$ $T_s = 80^\circ\text{C}$	21	A
Repetitive peak collector current	I_{CRM}	t_p limited by T_{jmax}	45	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ $T_s = 80^\circ\text{C}$	51	W
Gate-emitter voltage	V_{GES}		± 20	V
Short circuit ratings	t_{SC} V_{CC}	$T_j \leq 150^\circ\text{C}$ $V_{GE} = 15 \text{ V}$	6 360	μs V
Maximum junction temperature	T_{jmax}		175	$^\circ\text{C}$



10-FZ07BVA020SM-LD44E08
10-PZ07BVA020SM-LD44E08Y
target datasheet

Vincotech

Maximum Ratings

$T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Condition	Value	Unit
Boost Diode				
Peak repetitive reverse voltage	V_{RRM}		650	V
Continuous (direct) forward current	I_F	$T_j = T_{jmax}$ $T_s = 80^\circ\text{C}$	20	A
Repetitive peak forward current	I_{FRM}		30	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ $T_s = 80^\circ\text{C}$	39	W
Maximum junction temperature	T_{jmax}		175	$^\circ\text{C}$

Buck Switch

Collector-emitter voltage	V_{CES}		650	V
Collector current	I_C	$T_j = T_{jmax}$ $T_s = 80^\circ\text{C}$	24	A
Repetitive peak collector current	I_{CRM}	t_p limited by T_{jmax}	60	A
Turn off safe operating area		$T_j \leq 150^\circ\text{C}$, $V_{CE} \leq 650\text{ V}$	40	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ $T_s = 80^\circ\text{C}$	49	W
Gate-emitter voltage	V_{GES}		± 20	V
Maximum Junction Temperature	T_{jmax}		175	$^\circ\text{C}$

Buck Diode

Peak repetitive reverse voltage	V_{RRM}		650	V
Continuous (direct) forward current	I_F	$T_j = T_{jmax}$ $T_s = 80^\circ\text{C}$	20	A
Repetitive peak forward current	I_{FRM}		30	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ $T_s = 80^\circ\text{C}$	39	W
Maximum junction temperature	T_{jmax}		175	$^\circ\text{C}$



Vincotech

**10-FZ07BVA020SM-LD44E08
10-PZ07BVA020SM-LD44E08Y**
target datasheet

Maximum Ratings

$T_j = 25 \text{ } ^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Condition	Value	Unit
-----------	--------	-----------	-------	------

Module Properties

Thermal Properties

Storage temperature	T_{stg}		-40...+125	°C
Operation temperature under switching condition	T_{jop}		-40...(T _{jmax} - 25)	°C

Isolation Properties

Isolation voltage	V_{isol}	DC Test Voltage $t_p = 2 \text{ s}$	4000	V
Creepage distance			min. 12,7	mm
Clearance			9,89	mm
Comparative Tracking Index	CTI		> 200	



Vincotech

Characteristic Values

Parameter	Symbol	Conditions						Value			Unit	
		V_{GE} [V]	V_{CE} [V]	I_c [A]	I_D [A]	T_j [°C]	V_{GS} [V]	V_{DS} [V]	I_F [A]	Min	Typ	Max

Input Boost Switch

Static

Gate-emitter threshold voltage	$V_{GE(th)}$	$V_{GE}=V_{CE}$			0,0002	25		3,3	4	4,7	V
Collector-emitter saturation voltage	V_{CESat}		15		20	25 125 150		0,8	1,60 1,75 1,79	2,3	V
Collector-emitter cut-off current	I_{CES}		0	650		25				40	µA
Gate-emitter leakage current	I_{GES}		20	0		25				200	nA
Internal gate resistance	r_g								none		Ω
Input capacitance	C_{ies}	$f=1$ MHz	0	25	25				1200		pF
Output capacitance	C_{oes}								30		
Reverse transfer capacitance	C_{res}								5,2		
Gate charge	Q_g		15	520	20	25			48		nC

Thermal

Thermal resistance junction to sink	$R_{th(j-s)}$	phase-change material $\lambda = 3,4$ W/mK							1,94		K/W
-------------------------------------	---------------	---	--	--	--	--	--	--	------	--	-----

Input Boost Diode

Static

Forward voltage	V_F				20	25 125	0,8	1,56 1,51	2	V
Reverse leakage current	I_R			650		25			5	µA

Thermal

Thermal resistance junction to sink	$R_{th(j-s)}$	phase-change material $\lambda = 3,4$ W/mK							1,82		K/W
-------------------------------------	---------------	---	--	--	--	--	--	--	------	--	-----



Vincotech

Characteristic Values

Parameter	Symbol	Conditions						Value			Unit
		V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_c [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max			

Input Boost Sw. Protection Diode

Static

Forward voltage	V_F			6	25 125 150		1,73 1,59 1,54	1,87	V
Reverse leakage current	I_r		650		25			5	µA

Thermal

Thermal resistance junction to sink	$R_{th(j-s)}$	phase-change material $\lambda = 3,4 \text{ W/mK}$						3,51		K/W
-------------------------------------	---------------	---	--	--	--	--	--	------	--	-----

ByPass Diode

Static

Forward voltage	V_F			25	25 125		1,22 1,21		V
Reverse leakage current	I_r		1600		25 150			50 1100	µA

Thermal

Thermal resistance junction to sink	$R_{th(j-s)}$	phase-change material $\lambda = 3,4 \text{ W/mK}$						1,61		K/W
-------------------------------------	---------------	---	--	--	--	--	--	------	--	-----

Boost Switch

Static

Gate-emitter threshold voltage	$V_{GE(th)}$	$V_{GE} = V_{CE}$			0,00021	25	5,1	5,8	6,4	V
Collector-emitter saturation voltage	V_{CESat}		15		15	25	1	1,45	1,95	V
Collector-emitter cut-off current	I_{CES}		0	650		25			5	µA
Gate-emitter leakage current	I_{GES}		20	0		25			300	nA
Internal gate resistance	r_g							none		Ω
Input capacitance	C_{ies}	$f = 1 \text{ MHz}$	0	25	25			551		pF
Reverse transfer capacitance	C_{res}							17		

Thermal

Thermal resistance junction to sink	$R_{th(j-s)}$	phase-change material $\lambda = 3,4 \text{ W/mK}$						1,87		K/W
-------------------------------------	---------------	---	--	--	--	--	--	------	--	-----



10-FZ07BVA020SM-LD44E08
10-PZ07BVA020SM-LD44E08Y
target datasheet

Vincotech

Characteristic Values

Parameter	Symbol	Conditions						Value			Unit
			V_{GE} [V]	V_{CE} [V]	I_c [A]	I_D [A]	T_j [°C]	Min	Typ	Max	
			V_{GS} [V]	V_{DS} [V]	I_F [A]	I_F [A]					

Boost Diode

Static

Forward voltage	V_F				15	25	0,8	1,45	2	V
Reverse leakage current	I_R			650		25			5	μA

Thermal

Thermal resistance junction to sink	$R_{th(j-s)}$	phase-change material $\lambda = 3,4 \text{ W/mK}$						2,46		K/W
-------------------------------------	---------------	---	--	--	--	--	--	------	--	-----

Buck Switch

Static

Gate-emitter threshold voltage	$V_{GE(th)}$	$V_{GE}=V_{CE}$			0,0002	25	3,3	4	4,7	V
Collector-emitter saturation voltage	V_{CESat}		15		20	25 125 150	0,8	1,60 1,75 1,79	2,3	V
Collector-emitter cut-off current	I_{CES}		0	650		25			41	μA
Gate-emitter leakage current	I_{GES}		20	0		25			120	nA
Internal gate resistance	r_g							none		Ω
Input capacitance	C_{ies}	$f=1 \text{ MHz}$	0	25	25			1200		pF
Output capacitance	C_{oes}							30		
Reverse transfer capacitance	C_{res}							5,2		
Gate charge	Q_g		15	520	20	25		48		nC

Thermal

Thermal resistance junction to sink	$R_{th(j-s)}$	phase-change material $\lambda = 3,4 \text{ W/mK}$						1,94		K/W
-------------------------------------	---------------	---	--	--	--	--	--	------	--	-----

Buck Diode

Static

Forward voltage	V_F				15	25	0,8	1,45	2	V
Reverse leakage current	I_R			650		25			5	μA

Thermal

Thermal resistance junction to sink	$R_{th(j-s)}$	phase-change material $\lambda = 3,4 \text{ W/mK}$						2,46		K/W
-------------------------------------	---------------	---	--	--	--	--	--	------	--	-----



Vincotech

**10-FZ07BVA020SM-LD44E08
10-PZ07BVA020SM-LD44E08Y**
target datasheet

Characteristic Values

Parameter	Symbol	Conditions						Value			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_c [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max		

Thermistor

Rated resistance	R					25		22			kΩ
Deviation of R_{100}	$\Delta R/R$	$R_{100} = 1484 \Omega$				100	-5		5		%
Power dissipation	P					25		5			mW
Power dissipation constant						25		1,5			mW/K
B-value	$B_{(25/50)}$	Tol. ±1 %				25		3962			K
B-value	$B_{(25/100)}$	Tol. ±1 %				25		4000			K
Vincotech NTC Reference									I		



Vincotech

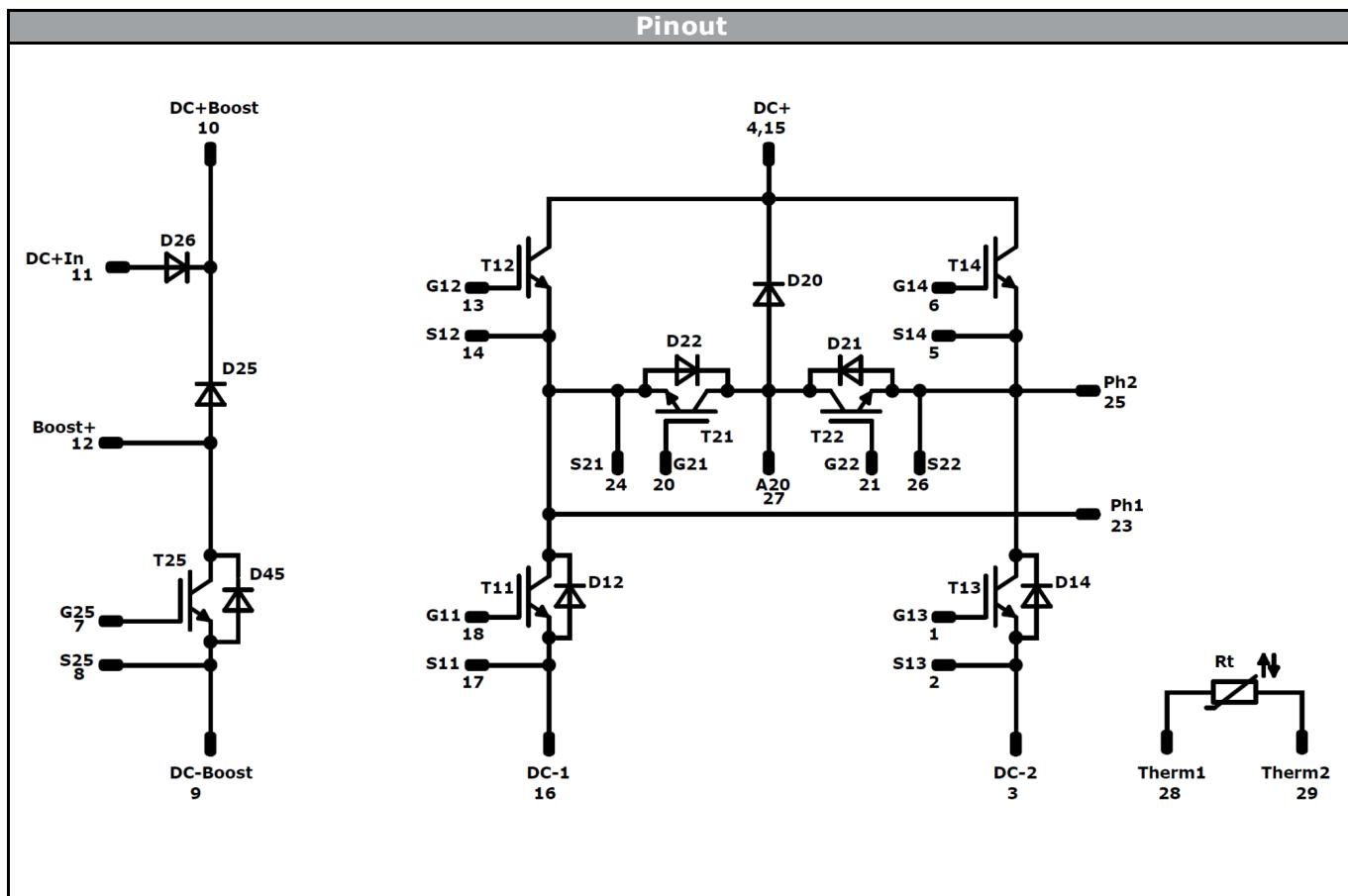
**10-FZ07BVA020SM-LD44E08
10-PZ07BVA020SM-LD44E08Y**
target datasheet

Ordering Code & Marking							
Version				Ordering Code			
with thermal paste 12mm housing with Solder pins				10-FZ07BVA020SM-LD44E08-/3/			
with thermal paste 12mm housing with Press-fit pins				10-PZ07BVA020SM-LD44E08Y-/3/			
NN-NNNNNNNNNNNN TTTTTVV WWYY UL VIN LLLL SSSS			Text	Name	Date code	UL & VIN	Lot
				NN-NNNNNNNNNNNN-TTTTTVV	WWYY	UL VIN	LLLLL
			Datamatrix	Type&Ver	Lot number	Serial	Date code
				TTTTTTTVV	LLLLL	SSSS	WWYY
Outline							
Pin table [mm]			Pin table [mm]				
Pin	X	Y	Function	Pin	X	Y	Function
1	28,7	0	G13	30	Not assembled		
2	25,9	0	S13				
3	23,1	0	DC-2				
4	17,6	0	DC+				
5	12,1	0	S14				
6	9,3	0	G14				
7	2,8	0	G25				
8	0	0	S25				
9	0	5,05	DC-Boost				
10	0	10,55	DC+Boost				
11	0	16,15	DC+In				
12	0	22,6	Boost+				
13	9,3	22,6	G12				
14	12,1	22,6	S12				
15	17,6	22,6	DC+				
16	23,1	22,6	DC-1				
17	25,9	22,6	S11				
18	28,7	22,6	G11				
19	Not assembled						
20	33,6	14,55	G21				
21	33,6	8,05	G22				
22	Not assembled						
23	33,6	17,35	Ph1				
24	30,8	14,55	S21				
25	33,6	5,25	Ph2				
26	30,8	8,05	S22				
27	17,6	14,1	A20				
28	11	8,5	Therm1				
29	10	11,5	Therm2				



10-FZ07BVA020SM-LD44E08
10-PZ07BVA020SM-LD44E08Y
target datasheet

Vincotech



Identification

ID	Component	Voltage	Current	Function	Comment
T25	IGBT	650 V	20 A	Input Boost Switch	
D25	FWD	650 V	20 A	Input Boost Diode	
D45	FWD	650 V	6 A	Input Boost Sw. Protection Diode	
D26	FWD	1600 V	25 A	ByPass Diode	
T21,T22	IGBT	650 V	15 A	Boost Switch	
D12,D14,D20	FWD	650 V	15 A	Boost Diode	
T11,T12,T13,T14	IGBT	650 V	20 A	Buck Switch	
D21,D22	FWD	650 V	15 A	Buck Diode	
Rt	Thermistor			Thermistor	



10-FZ07BVA020SM-LD44E08
10-PZ07BVA020SM-LD44E08Y
target datasheet

Vincotech

Packaging instruction			
Standard packaging quantity (SPQ) 135	>SPQ	Standard	<SPQ Sample

Handling instruction			
Handling instructions for flow 0 packages see vincotech.com website.			

Package data			
Package data for flow 0 packages see vincotech.com website.			

UL recognition and file number			
This device is certified according to UL 1557 standard, UL file number E192116. For more information see vincotech.com website.			

Document No.:	Date:	Modification:	Pages
10-FZ07BVA020SM-LD44E08-T1-14	27 Feb. 2017		

Product status definition		
Datasheet Status	Product Status	Definition
Target	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice. The data contained is exclusively intended for technically trained staff.

DISCLAIMER

The information, specifications, procedures, methods and recommendations herein (together "information") are presented by Vincotech to reader in good faith, are believed to be accurate and reliable, but may well be incomplete and/or not applicable to all conditions or situations that may exist or occur. Vincotech reserves the right to make any changes without further notice to any products to improve reliability, function or design. No representation, guarantee or warranty is made to reader as to the accuracy, reliability or completeness of said information or that the application or use of any of the same will avoid hazards, accidents, losses, damages or injury of any kind to persons or property or that the same will not infringe third parties rights or give desired results. It is reader's sole responsibility to test and determine the suitability of the information and the product for reader's intended use.

LIFE SUPPORT POLICY

Vincotech products are not authorised for use as critical components in life support devices or systems without the express written approval of Vincotech.

As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in labelling can be reasonably expected to result in significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.